

Silicon Fast Recovery Diode

 $V_{RRM} = 100\text{ V} - 600\text{ V}$
 $I_F = 85\text{ A}$

Features

- High Surge Capability
- Types up to 600 V V_{RRM}

DO-5 Package

Maximum ratings, at $T_j = 25\text{ }^\circ\text{C}$, unless otherwise specified ("R" devices have leads reversed)

Parameter	Symbol	Conditions	FR85B(R)02	FR85D(R)02	FR85G(R)02	FR85J(R)02	Unit
Repetitive peak reverse voltage	V_{RRM}		100	200	400	600	V
RMS reverse voltage	V_{RMS}		70	140	280	420	V
DC blocking voltage	V_{DC}		100	200	400	600	V
Continuous forward current	I_F	$T_C \leq 100\text{ }^\circ\text{C}$	85	85	85	85	A
Surge non-repetitive forward current, Half Sine Wave	$I_{F,SM}$	$T_C = 25\text{ }^\circ\text{C}$, $t_p = 8.3\text{ ms}$	1369	1369	1369	1369	A
Operating temperature	T_j		-40 to 125	-40 to 125	-40 to 125	-40 to 125	$^\circ\text{C}$
Storage temperature	T_{stg}		-40 to 150	-40 to 150	-40 to 150	-40 to 150	$^\circ\text{C}$

Electrical characteristics, at $T_j = 25\text{ }^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	FR85B(R)02	FR85D(R)02	FR85G(R)02	FR85J(R)02	Unit
Diode forward voltage	V_F	$I_F = 85\text{ A}$, $T_j = 25\text{ }^\circ\text{C}$	1.4	1.4	1.4	1.4	V
Reverse current	I_R	$V_R = 100\text{ V}$, $T_j = 25\text{ }^\circ\text{C}$	25	25	25	25	μA
		$V_R = 100\text{ V}$, $T_j = 125\text{ }^\circ\text{C}$	20	20	20	20	mA

Recovery Time

Maximum reverse recovery time	T_{RR}	$I_F = 0.5\text{ A}$, $I_R = 1.0\text{ A}$, $I_{RR} = 0.25\text{ A}$	200	200	200	250	nS
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